

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

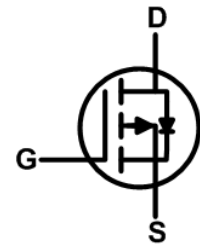
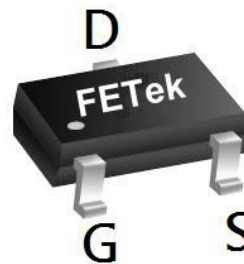
**Product Summary**


BVDSS	RDSON	ID
-30V	52mΩ	-3.3A

**Description**

The FKN3101 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The FKN3101 meet the RoHS and Green Product requirement, with full function reliability approved.

**SOT23 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating		Units
		10s	Steady State	
$V_{DS}$	Drain-Source Voltage	-30		V
$V_{GS}$	Gate-Source Voltage	±20		V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.8	-3.3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.1	-2.7	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-17		A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	1.32	1	W
$P_D@T_A=70^\circ C$	Total Power Dissipation <sup>3</sup>	0.84	0.64	W
$T_{STG}$	Storage Temperature Range	-55 to 150		°C
$T_J$	Operating Junction Temperature Range	-55 to 150		°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	125	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)	---	95	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.023	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-3A$	---	42	52	$\text{m}\Omega$
		$V_{GS}=-4.5V, I_D=-2A$	---	75	90	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4	---	$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V, I_D=-3A$	---	11	---	S
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-3A$	---	6.4	9.0	nC
$Q_{gs}$	Gate-Source Charge		---	2.3	3.2	
$Q_{gd}$	Gate-Drain Charge		---	1.9	2.7	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-3A$	---	2.8	5.6	ns
$T_r$	Rise Time		---	8.4	15.1	
$T_{d(off)}$	Turn-Off Delay Time		---	39	78.0	
$T_f$	Fall Time		---	6	12.0	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	583	816	pF
$C_{oss}$	Output Capacitance		---	100	140	
$C_{rss}$	Reverse Transfer Capacitance		---	80	112	

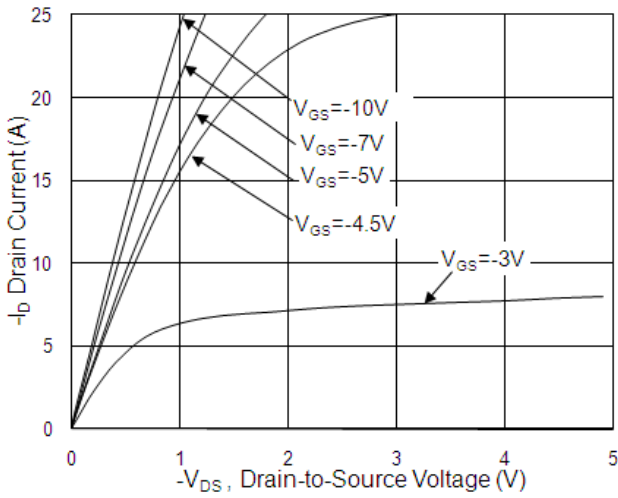
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	-3.3	A
$I_{SM}$	Pulsed Source Current <sup>2,4</sup>		---	---	-17	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
$t_{rr}$	Reverse Recovery Time	$I_F=-3A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	7.8	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	2.5	---	nC

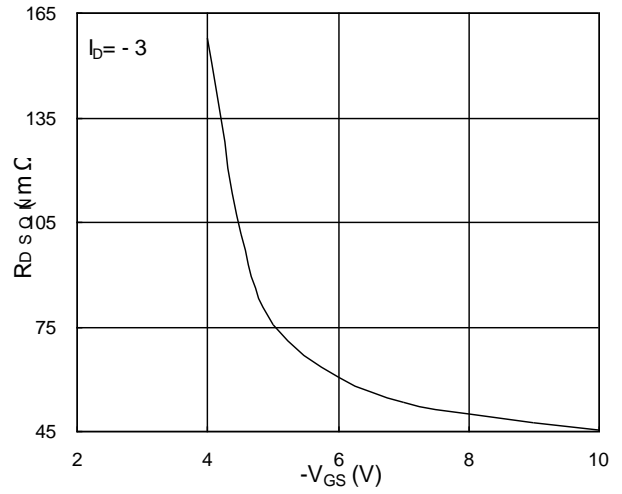
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.

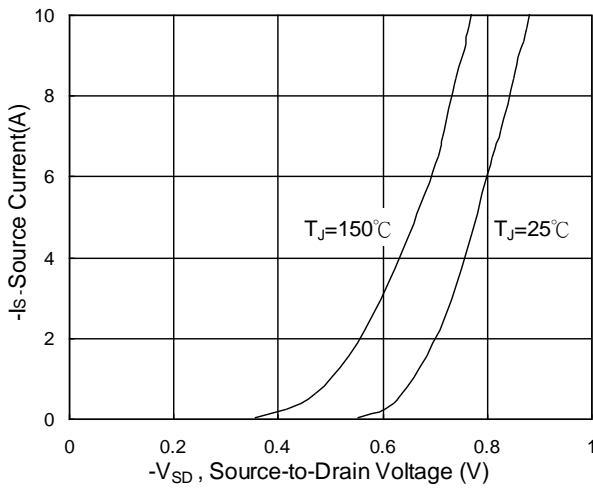
**Typical Characteristics**



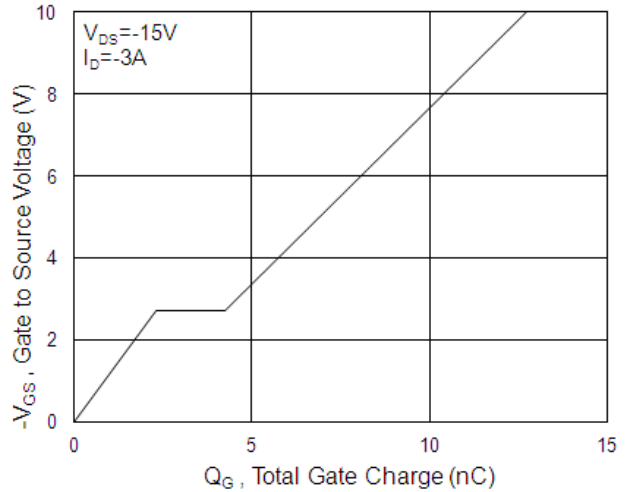
**Fig.1 Typical Output Characteristics**



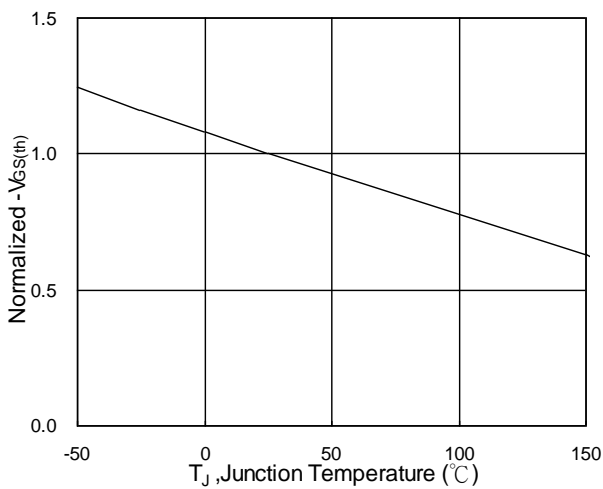
**Fig.2 On-Resistance v.s Gate-Source**



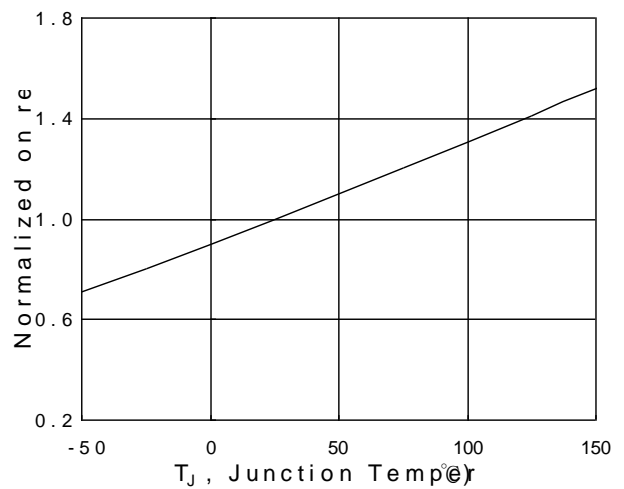
**Fig.3 Forward Characteristics of Reverse**



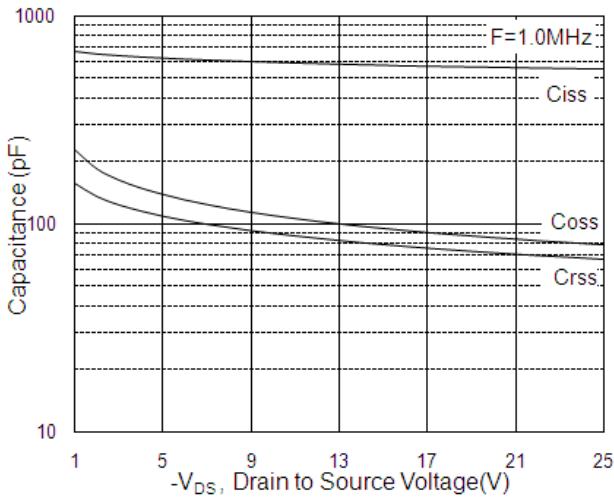
**Fig.4 Gate-Charge Characteristics**



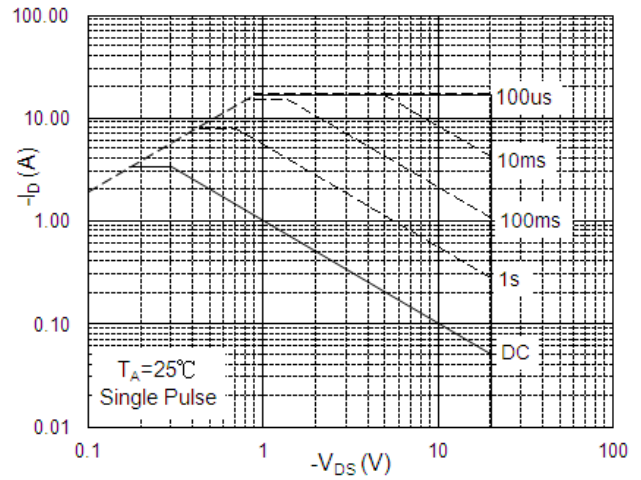
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



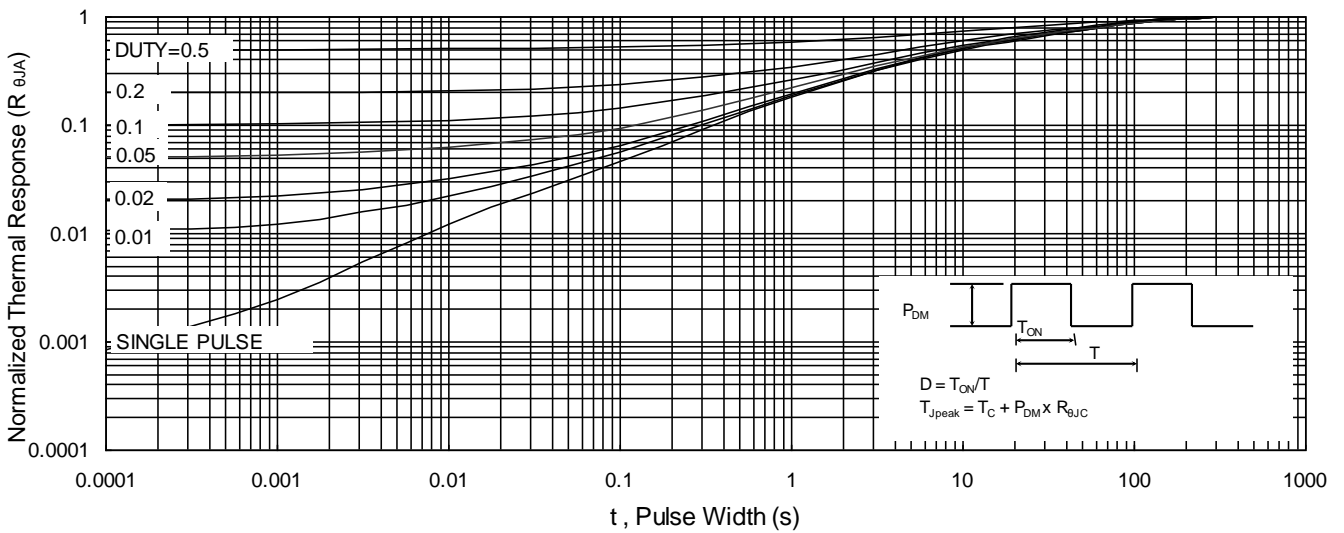
**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**



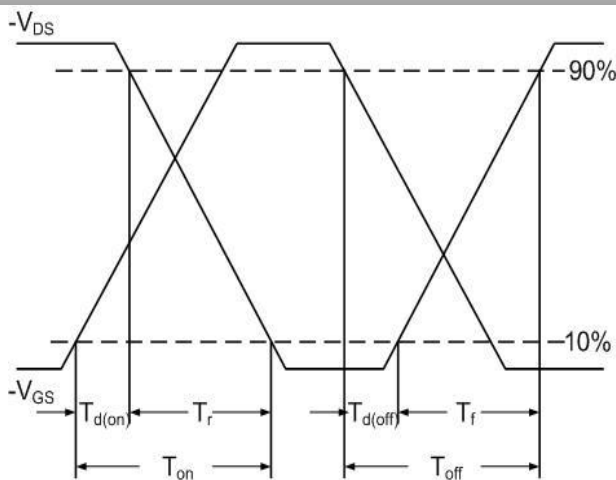
**Fig.7 Capacitance**



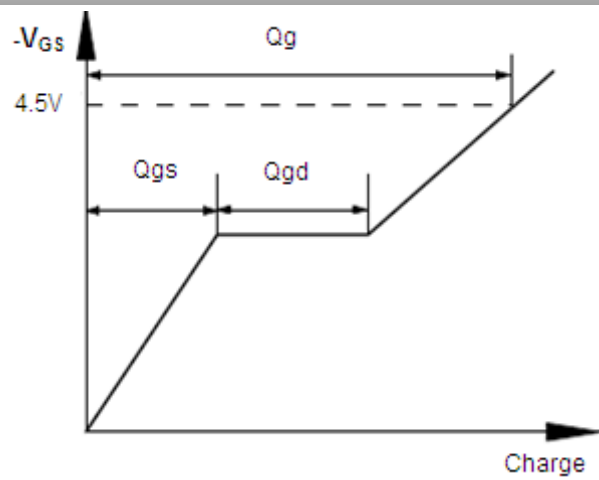
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**